

EAST - [10718691.wsp:1]

File View Edit Tools Window Help

Drafts
BRS
Pending
Active
L1: (482) silicon adj carbide and (metal
L2: (522) silicon adj carbide and (metal
L3: (9) 2 and laser adj ablation
L4: (7310) laser adj ablation
L5: (8) 4 and (electrode with (silicon adj
L6: (13) 4 and (electrode and (silicon ad
L7: (17) 4 and ((silicon adj carbide) and
L9: (0) 4 and ((silicon adj carbide with s
L10: (5) 4 and ((silicon adj carbide with
L11: (2) laser adj ablation with metal adj
L12: (49) laser adj ablation and (metal a
L13: (11) 12 and (silicon adj carbide "SiC"
L15: (25) 14 and (silicon adj carbide "SiC"
L16: (3) laser adj ablation and ("PtSi" an
L17: (3) laser adj ablation with (metal w
L18: (2) laser adj ablation with (metal ac
L14: (78) laser adj ablation and (metal v
L19: (78) 4 and (metal with silicide)
L20: (47) 19 and electrode
L21: (11) 20 and (silicon adj carbide "SiC"
Failed
(0) 4 and (electrode with (silicon adj cart
(2) 4 and ((silicon adj carbide with subs
Saved
Favorites

Browse Queue Clear

DBs: USPAT, EPO, JPO, DERWENT, IBM, TDB

Plurals

Default operator: OR

Highlight all hit terms initially

20 and (silicon adj carbide "SiC")

BRST I56R Image Text HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6627964 B2	20030930	15	Gas sensor	257/414	257/565; 257/769;
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6426512 B1	20020730	45	Group III nitride compound semiconductor device	257/12	257/103; 257/13;
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6425993 B1	20020730	25	Membrane electrode assembly and method of its manufacture	204/296	204/283; 428/421;
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6316873 B1	20011113	17	Electron emission device and display device using the same	313/496	313/309; 313/310;
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6042959 A	20000328	25	Membrane electrode assembly and method of its manufacture	429/33	204/283; 204/296;
6	<input type="checkbox"/>	<input type="checkbox"/>	US 5937318 A	19990810	42	Monocrystalline three-dimensional integrated circuit	438/505	257/E21.092; 257/E21.537;
7	<input type="checkbox"/>	<input type="checkbox"/>	US 5739563 A	19980414	26	Ferroelectric type semiconductor device having a barium titanate type dielectric film	257/295	257/E21.009; 257/E21.664;
8	<input type="checkbox"/>	<input type="checkbox"/>	US 5726524 A	19980310	25	Field emission device having nanostructured emitters	313/309	204/192.1; 204/192.38;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 5474619 A	19951212	11	Thin film high temperature silicide thermocouples	136/239	136/201; 136/225
10	<input type="checkbox"/>	<input type="checkbox"/>	JP 2002289555 A	20021004	9	ELECTRODE FOR, SILICON CARBIDE SEMICONDUCTOR, SILICON CARBIDE		
11	<input type="checkbox"/>	<input type="checkbox"/>	EP 1246252 A2	20021002	13	Electrode for silicon carbide semiconductor, silicon carbide semiconductor element		